Sebastian Heedt

List of Publications by Citations

24 papers	403 citations	11 h-index	20 g-index
28 ext. papers	537 ext. citations	9.4 avg, IF	3.26 L-index

#	Paper	IF	Citations
24	Signatures of interaction-induced helical gaps in nanowire quantum point contacts. *Nature Physics*, **2017**, 13, 563-567	16.2	57
23	Selectivity Map for Molecular Beam Epitaxy of Advanced III-V Quantum Nanowire Networks. *Nano Letters*, **2019**, 19, 218-227	11.5	51
22	Ballistic Transport and Exchange Interaction in InAs Nanowire Quantum Point Contacts. *Nano Letters*, **2016**, 16, 3116-23	11.5	37
21	Electrical spin injection into InN semiconductor nanowires. *Nano Letters*, **2012**, 12, 4437-43	11.5	31
20	Parity transitions in the superconducting ground state of hybrid InSb-Al Coulomb islands. *Nature Communications*, **2018**, 9, 4801	17.4	28
19	Amphoteric nature of Sn in CdS nanowires. *Nano Letters*, **2014**, 14, 518-23	11.5	27
18	Resolving ambiguities in nanowire field-effect transistor characterization. *Nanoscale*, **2015**, 7, 18188-97	7.7	25
17	Crystal Phase Transformation in Self-Assembled InAs Nanowire Junctions on Patterned Si Substrates. *Nano Letters*, **2016**, 16, 1933-41	11.5	24
16	Adiabatic Edge Channel Transport in a Nanowire Quantum Point Contact Register. *Nano Letters*, **2016**, 16, 4569-75	11.5	23
15	Weak (anti)localization in tubular semiconductor nanowires with spin-orbit coupling. *Physical Review B*, **2016**, 93,	3.3	21
14	High Mobility Stemless InSb Nanowires. *Nano Letters*, **2019**, 19, 3575-3582	11.5	18
13	Frequency anomaly in the Rashba-effect induced magnetization oscillations of a high-mobility two-dimensional electron system. *Physical Review B*, **2013**, 87,	3.3	9
12	Electronic Properties of Complex Self-Assembled InAs Nanowire Networks. *Advanced Electronic Materials*, **2016**, 2, 1500460	6.4	9
11	Shadow-wall lithography of ballistic superconductor-semiconductor quantum devices. *Nature Communications*, **2021**, 12, 4914	17.4	8
10	Magnetoconductance correction in zinc-blende semiconductor nanowires with spin-orbit coupling. *Physical Review B*, **2017**, 96,	3.3	7
9	Electrical properties of lightly Ga-doped ZnO nanowires. *Semiconductor Science and Technology*, **2017**, 32, 125010	1.8	6
8	Impact of Tunnel-Barrier Strength on Magnetoresistance in Carbon Nanotubes. *Physical Review Applied*, **2016**, 5,	4.3	5

List of Publications

7	Full parity phase diagram of a proximitized nanowire island. *Physical Review B*, **2021**, 104,	3.3	5
6	Dresselhaus spin-orbit coupling in [111]-oriented semiconductor nanowires. *Physical Review B*, **2019**, 99,	3.3	5
5	Exfoliated hexagonal BN as gate dielectric for InSb nanowire quantum dots with improved gate hysteresis and charge noise. *Applied Physics Letters*, **2020**, 116, 253101	3.4	2
4	Transmission phase read-out of a large quantum dot in a nanowire interferometer. *Nature Communications*, **2020**, 11, 3666	17.4	2
3	Confinement and inhomogeneous broadening effects in the quantum oscillatory magnetization of quantum dot ensembles. *Journal of Physics Condensed Matter*, **2016**, 28, 045301	1.8	2
2	Single-Shot Fabrication of SemiconductingSuperconducting Nanowire Devices. *Advanced Functional Materials*, **2021**, 31, 2102388	15.6	1
1	Toward Spin Electronic Devices Based on Semiconductor Nanowires328-339		